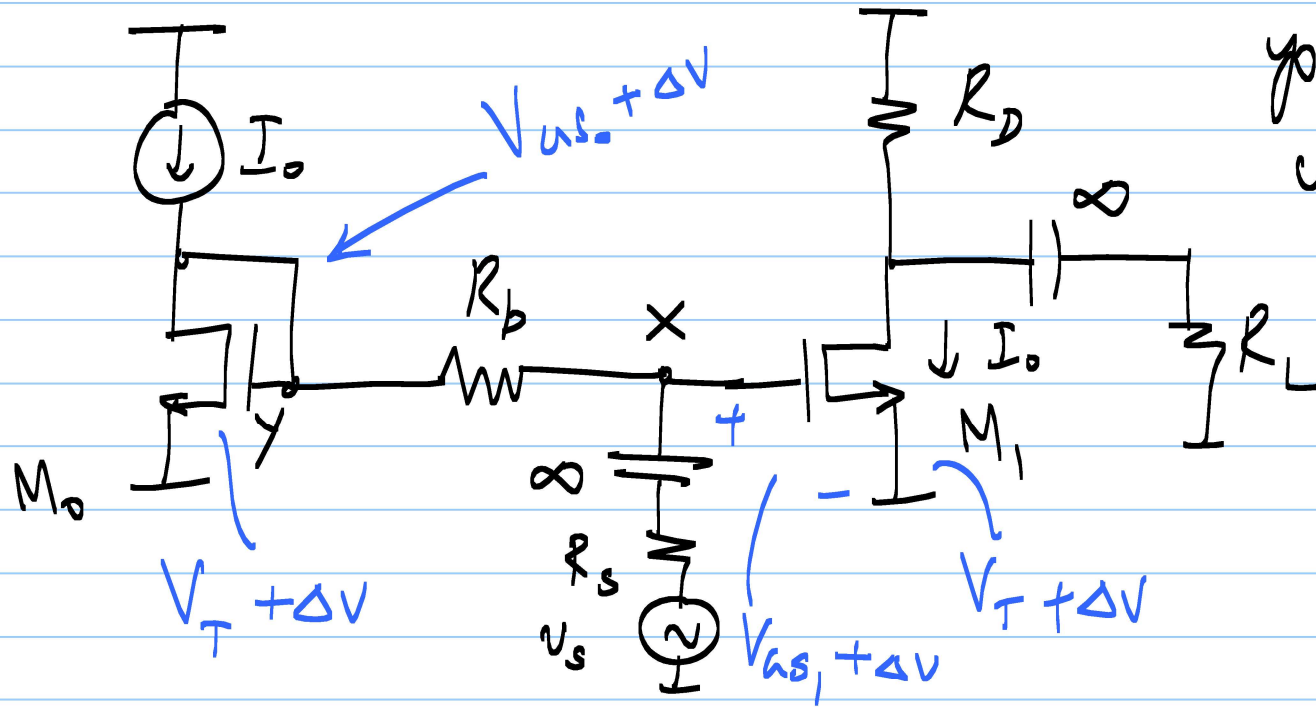


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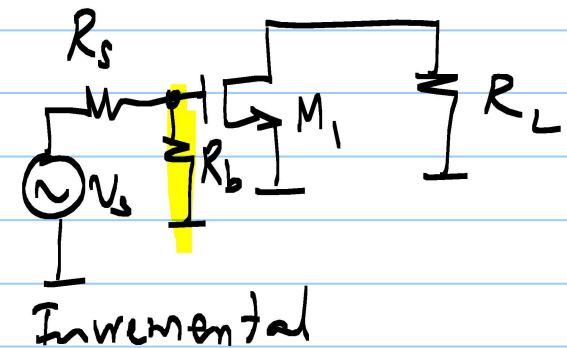
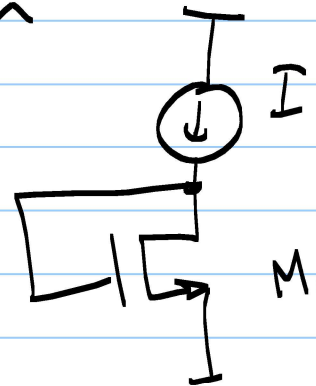
Lecture 15

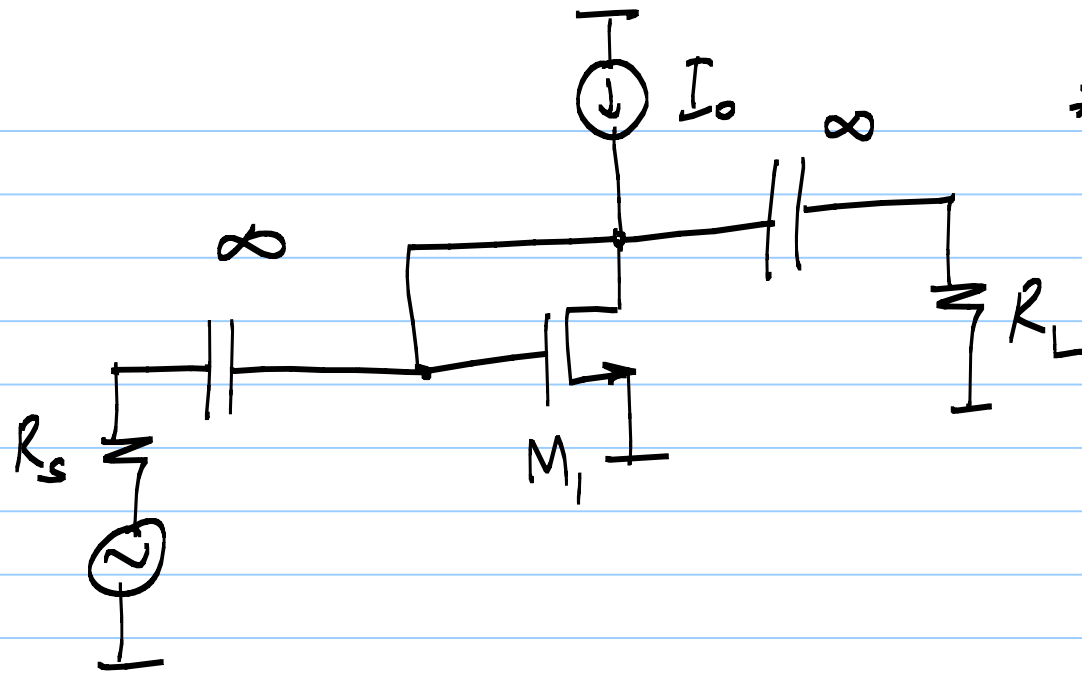
* If V_{T1} changes by ΔV ,
you expect V_{T0} to also
change by ΔV



Can you do this with
a single MOSFET?

DC bias





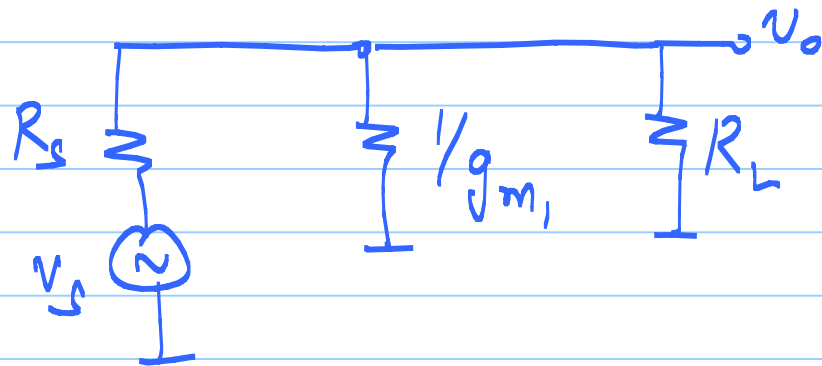
* Start with DC bias

circuit

* Add source & load

* $V_{DS} = V_{AS}$

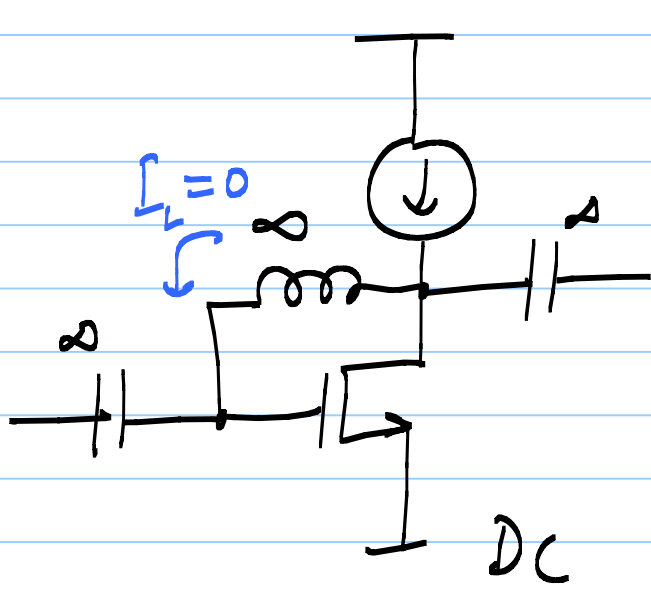
* M_1 is in sat.



$$\frac{v_o}{v_s} = \frac{R_L \parallel 1/g_{m1}}{R_s + R_L \parallel 1/g_{m1}}$$

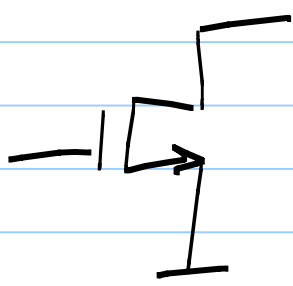
Not what we want!

Options: 1) Add ∞ inductor between G & D

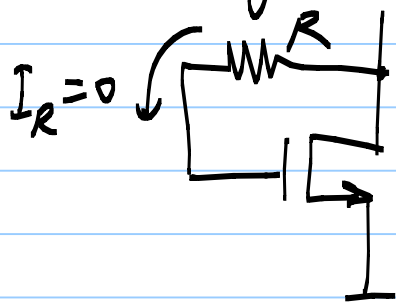


✓ AC

works but impractical (L's are bulky)



2) V_{GS} large resistor (because $I_L = 0$)

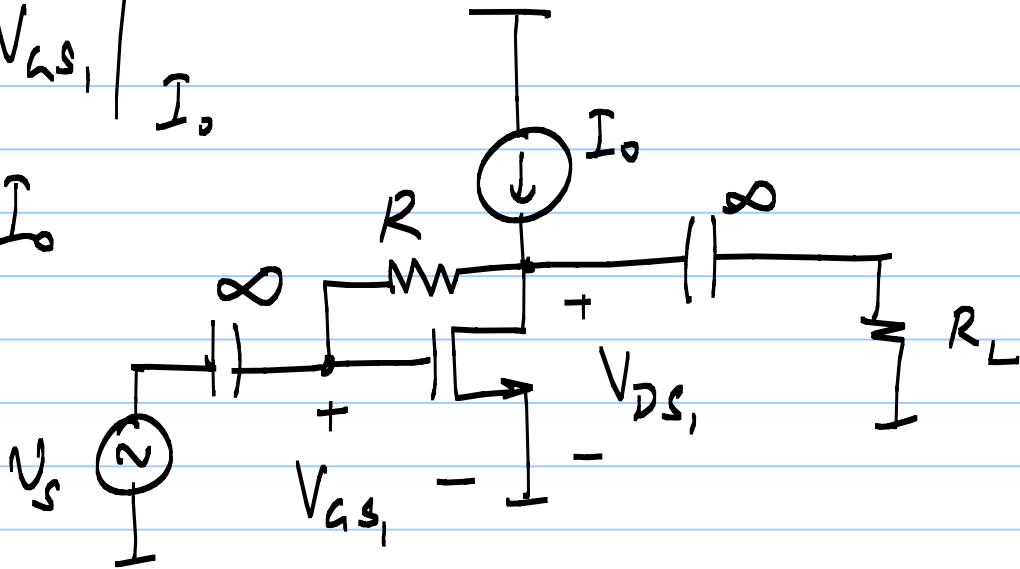


$V_{DS_1} = V_{GS_1}$, feedback maintained

$$V_{DS,1} = V_{GS,1} / I_0$$

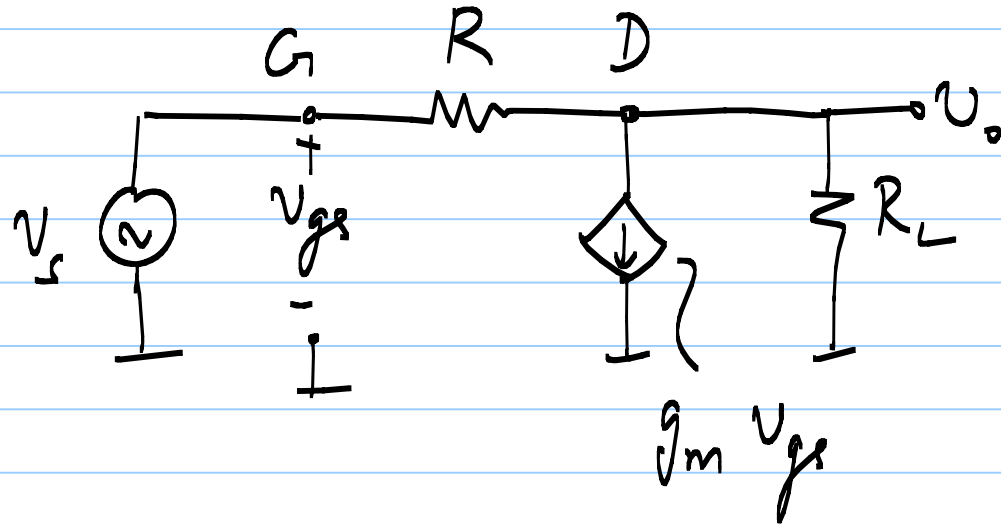
$$I_{D,1} = I_0$$

DC is okay



HW1 : Analyse
with R_s

SS eq.:



$$v_{gs} = v_s$$

KCL @ drain node :

$$\frac{v_s - v_o}{R} = g_m v_s + \frac{v_o}{R_L}$$

$$\frac{1}{R} = G, \quad \frac{1}{R_L} = G_L$$

$$v_s [G - g_m] = v_o [G_L + G]$$

$$\frac{v_o}{v_s} = \frac{G - g_m}{G + G_L} = \frac{-g_m}{G_L} \underbrace{\left[\frac{1 - G/g_m}{1 + G/G_L} \right]}$$

We want

* $g_m \gg G_L$ (large gain)

* $G \ll G_L \Rightarrow G \ll g_m$

By "large R ", we mean $R \gg R_L$

$$\text{gain} \approx -g_m R_L$$

≈ 1 (desired)

Swing limits:

* Triode limit is lower because $V_{DS} = V_{GS}$

* Cutoff limit is same as before; $I_D = \text{same}$ as before

